

# Qub-IT meeting

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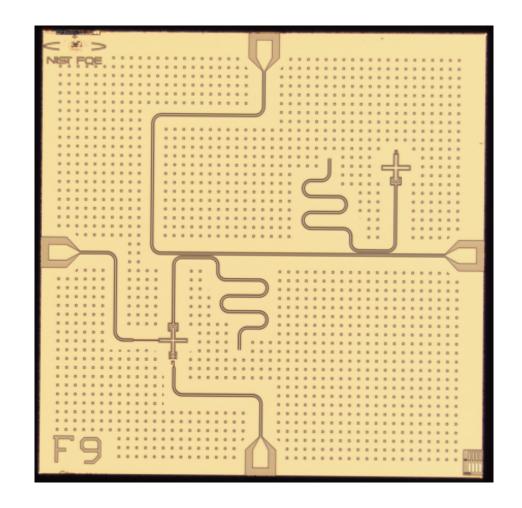
Thanks to the Superconductive Electronics Group

- Fabrication: David Olaya
- Measurements: Manuel Beltran Castellanos
  Adam Sirois, Pete Hopkins, Samuel Benz

## The first design

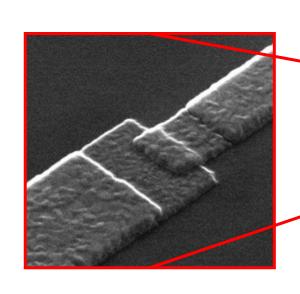
#### Goals:

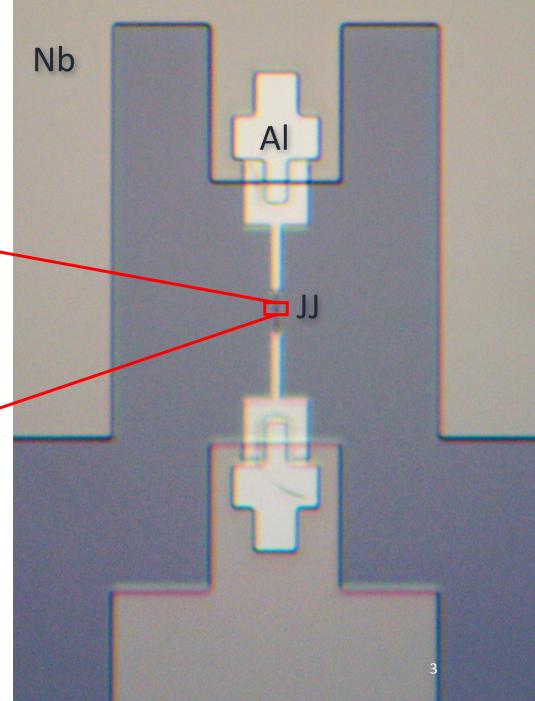
- Test simulation/measurement agreement
- Verify the ability to control the qubit state
- Measure the coherence times
- Measure qubit/cavity couplings
- Test qubit tunability and mutual inductance



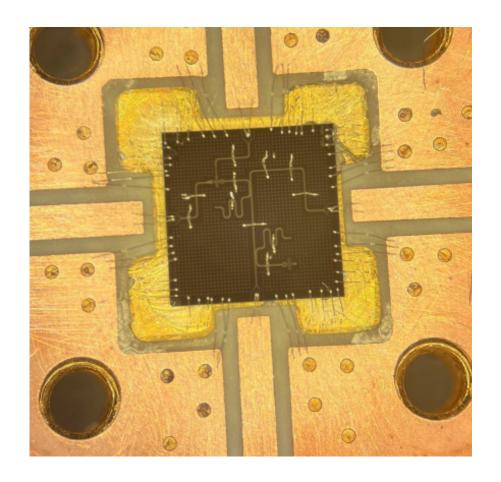
#### Qubit fabrication @ NIST

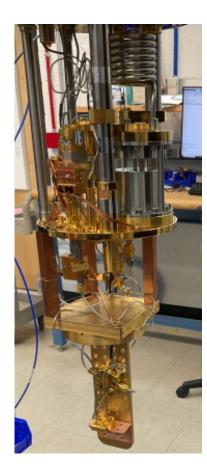
- Substrate: 380 nm high-resistive silicon
- Metal: 100 nmNiobium
- Junctions: Al-AlOx Al
- Niobium etched also in the JJ area





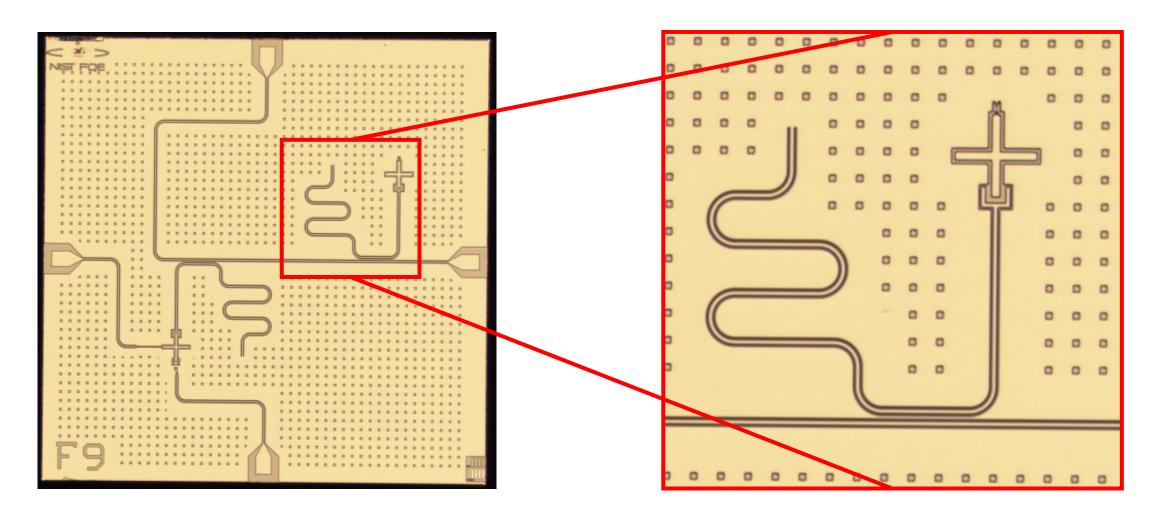
## Qubit measurements @ NIST







## Single JJ qubit



## Single JJ qubit – Cavity spectroscopy

•• 
$$f_r = 7.573 \; GHz$$

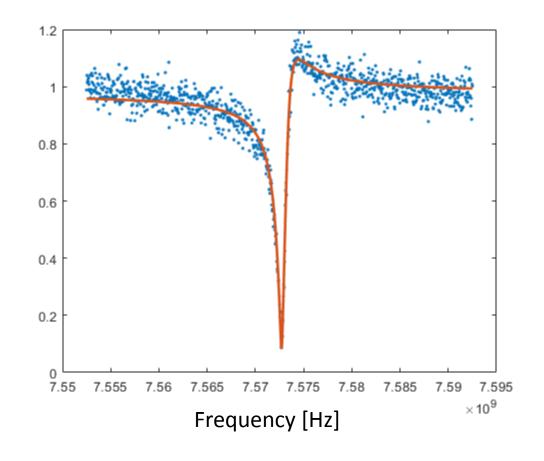
• 
$$Q_i = 5.624 \times 10^4$$

• 
$$Q_C = 5.063 \times 10^3$$

• 
$$\phi = -0.5099 \, rad$$

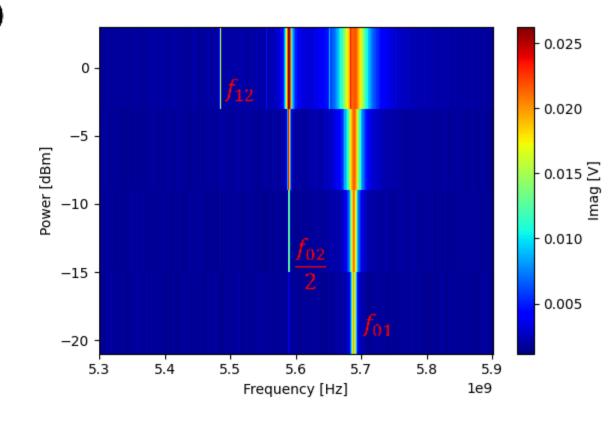
• 
$$A = 0.9759$$

Low internal quality factor: suspects on this wafer because of other design showing same problems



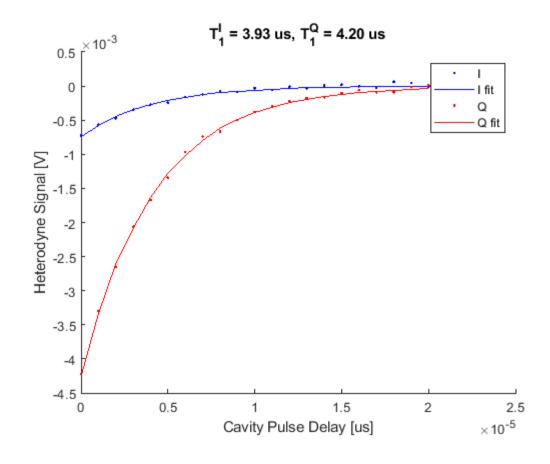
## Single JJ qubit – Qubit spectroscopy

- Val = Measured (LOM closest frequency)
- $f_{01} = 5.689 \, GHz \, (5.682 GHz)$
- $\frac{f_{02}}{2}$  = 5.589 *GHz* (5.579 *GHz*)
- $f_{12} = 5.485 \ GHz \ (5.476 \ GHz)$
- $\bullet \frac{\alpha}{2\pi} = -204 \, MHz \, (-206 \, MHz)$
- $L_I = 7.641 \, nH \, (7.2 \, nH)$

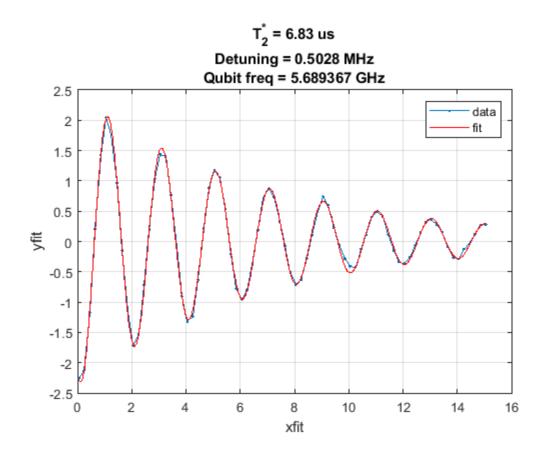


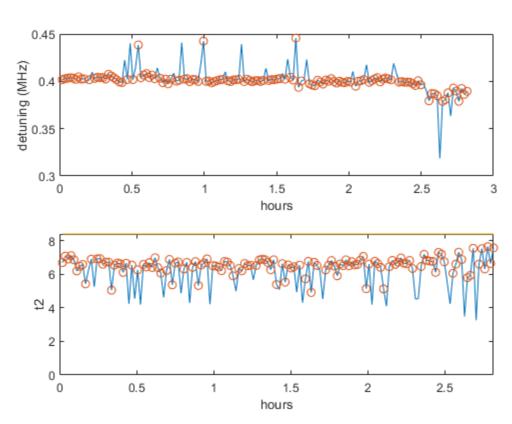
## Single JJ qubit – T<sub>1</sub> measurements

- Low T<sub>1</sub> related to low Q<sub>i</sub>, suspected fabrication issue
- Different designs showed the same issue
- Expected T<sub>1</sub> from Purcell should be about 40 us
- New production will be done

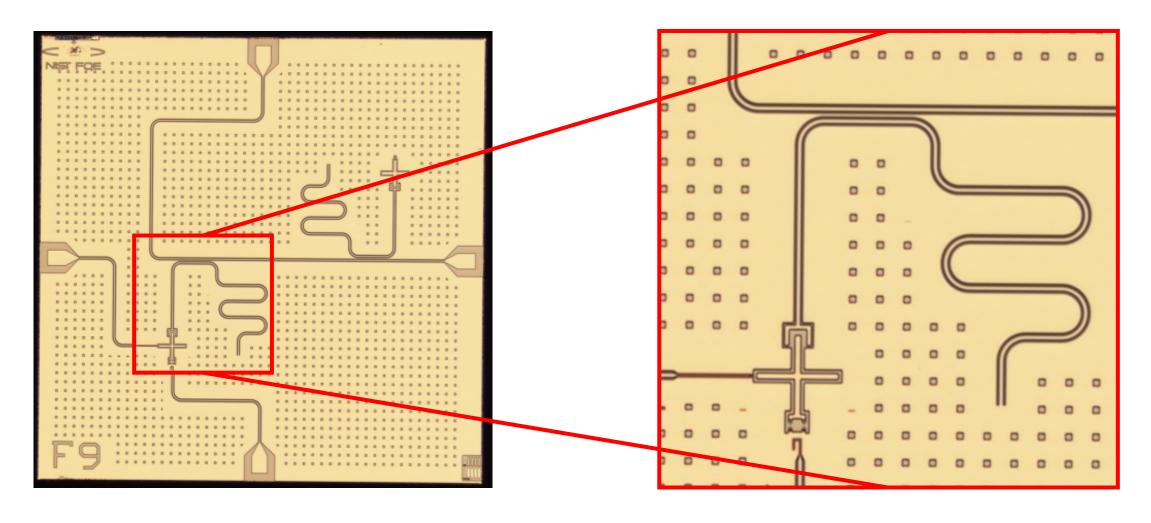


## Single JJ qubit – T<sub>2</sub> measurements





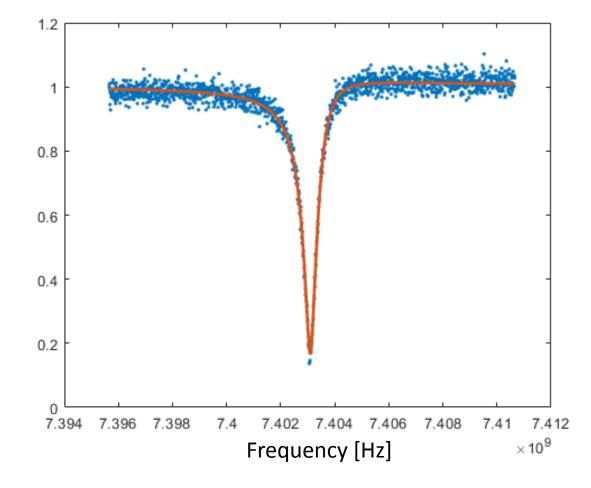
## SQUID qubit



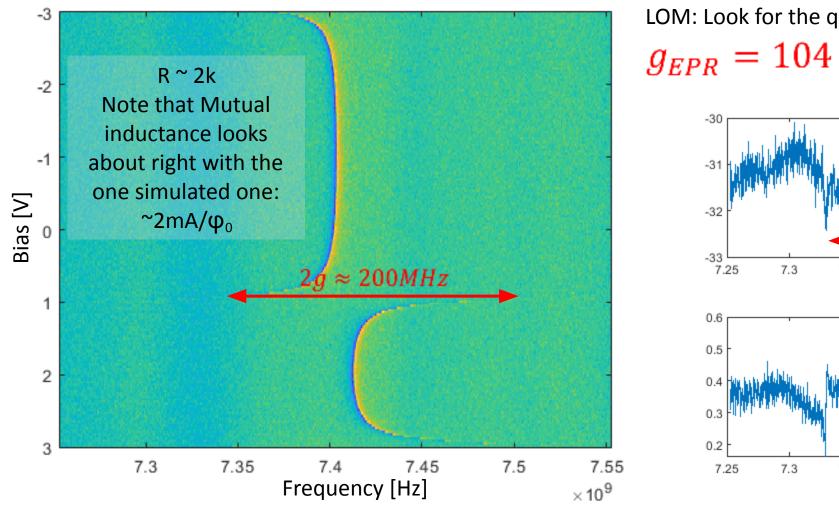
## SQUID qubit – Cavity spectroscopy

- ••  $f_r = 7.403 \; GHz$ 
  - $Q_i = (4.927 \pm 0.339) \times 10^4$
  - $Q_C = (9.673 \pm 0.124) \times 10^3$
  - $\phi = -0.1634 \pm 0.078 \, rad$
  - $A = 1.003 \pm 0.001$

Low internal quality factor: suspects on this wafer because of other design showing same problems

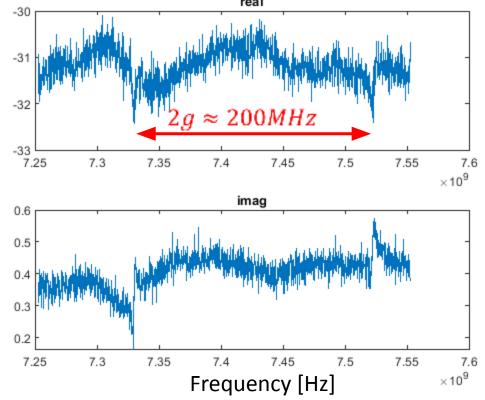


### SQUID qubit – Cavity spectroscopy



LOM: Look for the quarter-wave resonator (factor of 2)

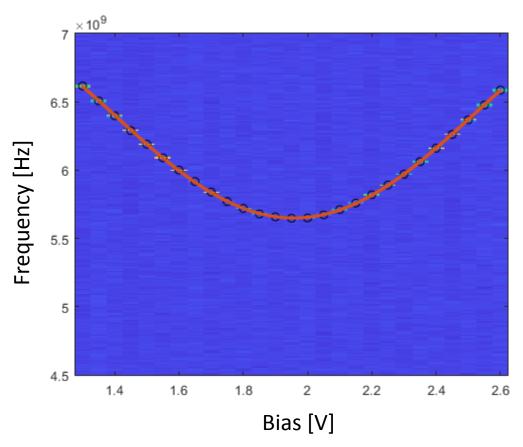
 $g_{EPR} = 104 MHz \ g_{LOM} \approx 49 MHz$ 



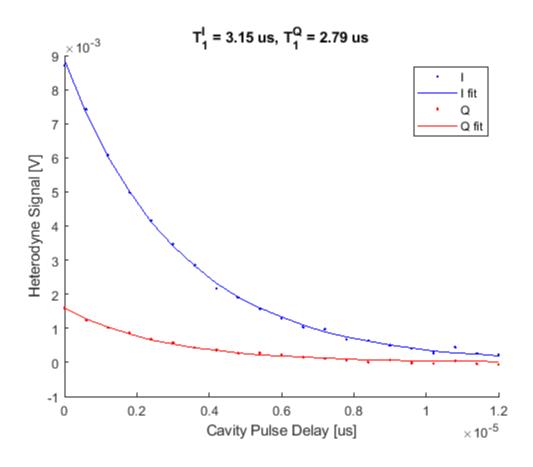
10/23/2023

## SQUID qubit – Qubit spectroscopy

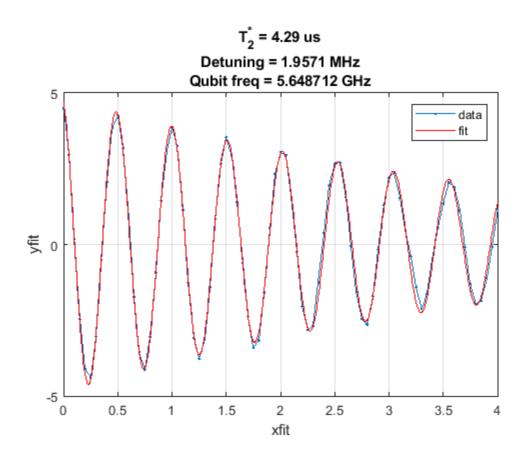
- Val = Measured (LOM closest frequency)
- $f_{01}^{MIN} = 5.649 \ GHz \ (5.649 \ GHz)$
- $L_I = 8.364 \ nH \ (7.9 \ nH)$

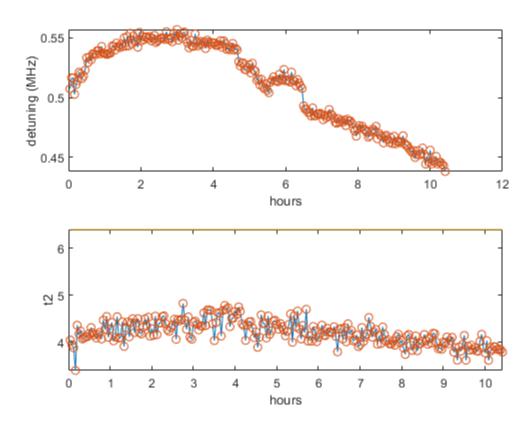


## SQUID qubit – T<sub>1</sub> measurements



## SQUID qubit – T<sub>2</sub> measurements

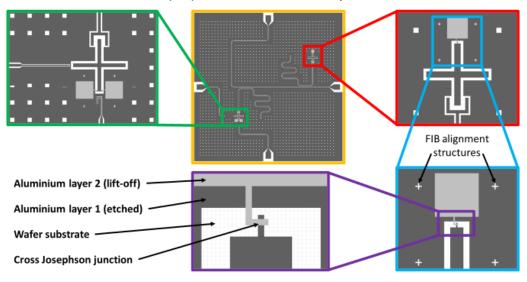




### Design adapted for qubit fabrication @ FBK

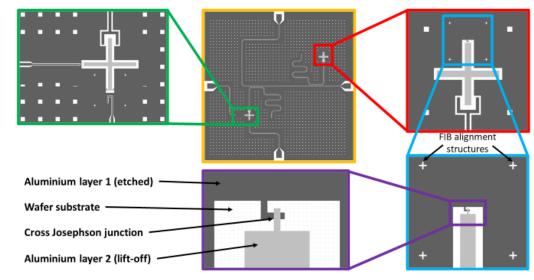
#### Qubit design adapted to FBK fabrication process - design 1

Cross-JJ area limited to  $\ge 3x3 \ \mu m^2$  (mask lithography @ FBK)  $\rightarrow$  use Focused Ion Beam (FIB) to reduce JJ area after production



#### Qubit design adapted to FBK fabrication process – design 2

Cross-JJ area limited to  $\geq$  3x3  $\mu$ m<sup>2</sup> (mask lithography @ FBK)  $\rightarrow$  use Focused Ion Beam (FIB) to reduce JJ area after production



## Conclusions and future perspectives

- Simulations and measurements are in good agreement
- All predicted frequencies and couplings are close to the measured ones
- New wafer production will be done to confirm low T1 and Qi was due to fabrication and not design issue (note: contribution could also come from fridge grounding, to be investigated)
- Flux line contribution to dissipation could be an issue, we may need to investigate it more
- Same design was adapted for FBK fabrication
- Coupled qubits design is under development